

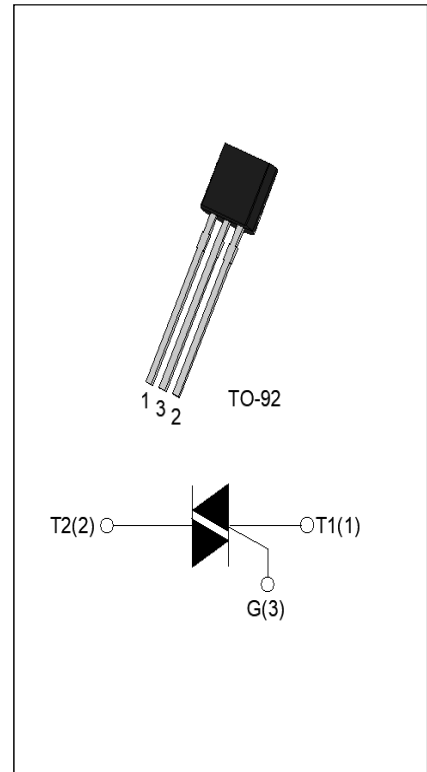
**BT131-800E**
**MAIN FEATURES      4Q TRIAC**

Symbol	Value	Unit
$I_{T(RMS)}$	1	A
$V_{DRM}/V_{RRM}$	800	V
$I_{GT1/2/3}$	10/10/10/25	mA

**DESCRIPTION:**

The BT131-800E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers.

Package TO-92 is RoHS compliant.


**ABSOLUTE MAXIMUM RATINGS**

Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	°C
Operating junction temperature range	$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	800	V
RMS on-state current ( $T_c \leq 90^\circ\text{C}$ )	$I_{T(RMS)}$	1	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	12	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	0.72	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $T_j=125^\circ\text{C}$ )	$di/dt$	50	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=125^\circ\text{C}$ )	$I_{GM}$	1	A
Average gate power dissipation ( $T_j=125^\circ\text{C}$ )	$P_{G(AV)}$	0.2	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^\circ\text{C}$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V$ $R_L=100\Omega$	I - II - III	MAX.	10	mA
		IV		25	
$V_{GT}$		ALL	MAX.	1.3	V
$V_{GD}$	$V_D=V_{DRM}$ $T_j=125^\circ\text{C}$ $R_L=100\Omega$	ALL	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I - III - IV	MAX.	10	mA
		II		30	
$I_H$	$I_T=500\text{mA}$		MAX.	20	mA
dV/dt	$V_D=2/3V_{DRM}$ $T_j=125^\circ\text{C}$		MIN.	500	V/ $\mu\text{s}$
dV/dt	$T_j=125^\circ\text{C}$		MIN.	10	V/ $\mu\text{s}$

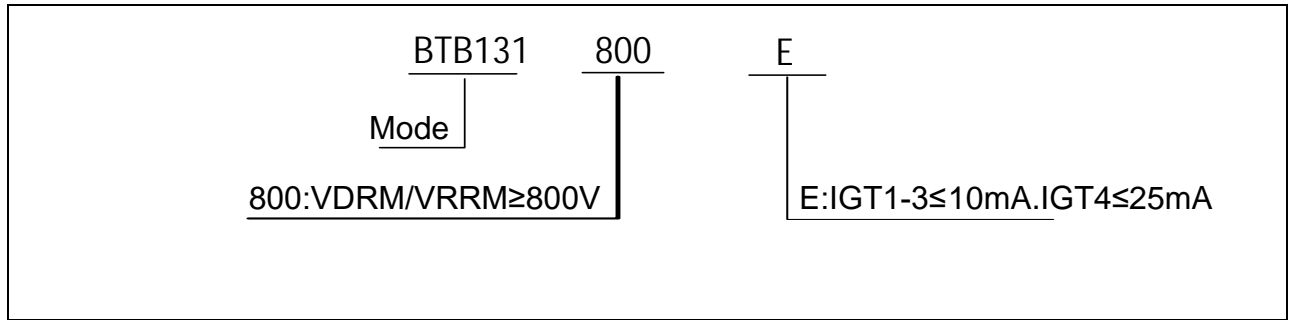
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=32\text{A}$	$T_j=25^\circ\text{C}$	1.40	V
$V_{TO}$	Threshold voltage	$T_j=125^\circ\text{C}$	0.94	V
$R_D$	Dynamic resistance	$T_j=125^\circ\text{C}$	36.8	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM}$ $V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	$\mu\text{A}$
$I_{RRM}$		$T_j=125^\circ\text{C}$	1	mA

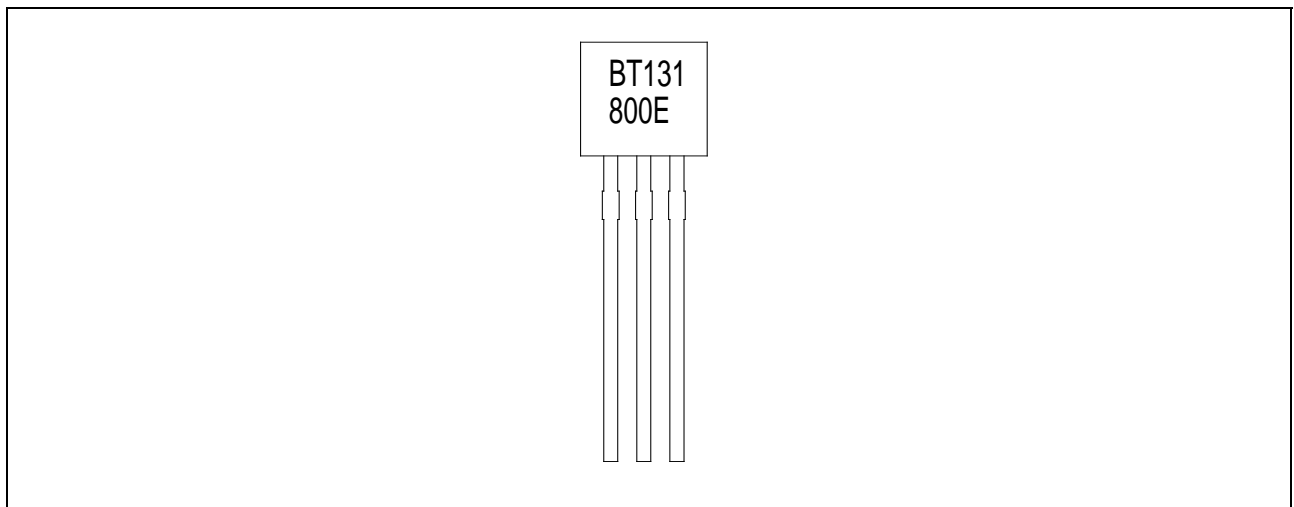
**THERMAL RESISTANCES**

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	11.3	$^\circ\text{C}/\text{W}$

**ORDERING INFORMATION**



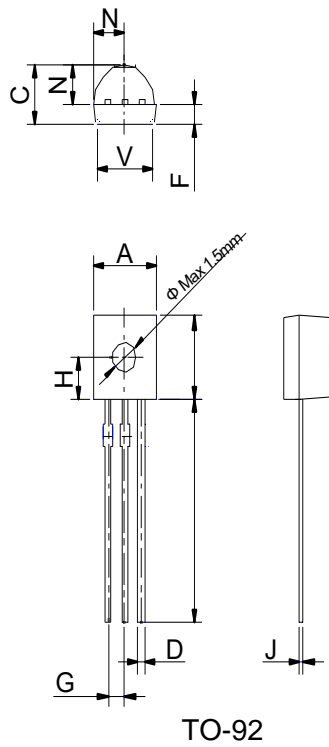
**MARKING**



**ORDERING INFORMATION**

Order code	Voltage V <sub>DRM</sub> /V <sub>R<sub>RRM</sub></sub> (V)	IGT(mA)		Package	Base qty. (pcs)	Delivery mode
		I -II-III	IV			
BT131-800E	800	10	25	TO-92	/	/

PACKAGE MECHANICAL DATA

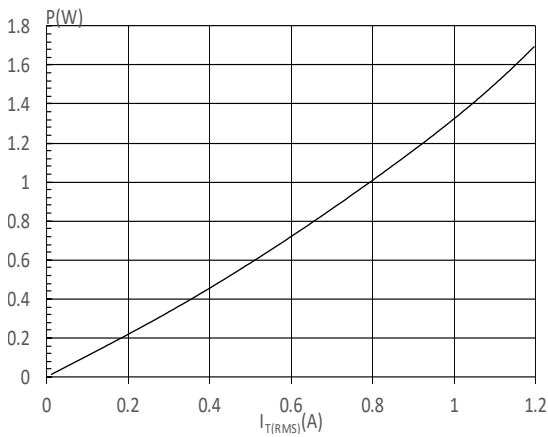


Ref.	Dimensions		
	Millimeters		
	Min.	Typ.	Max.
A	4.43	4.58	4.83
B	4.38	4.58	4.78
C	/	/	3.86
D	0.45	0.46	0.47
F	8.97	9.17	9.37
G	9.96	10.16	10.36
H	6.48	6.68	6.88
J	2.44	2.54	2.64
K	28.65	28.95	29.25
N	1.10	1.30	1.50
P	3.15	3.30	3.45
V	3.15	3.30	3.45

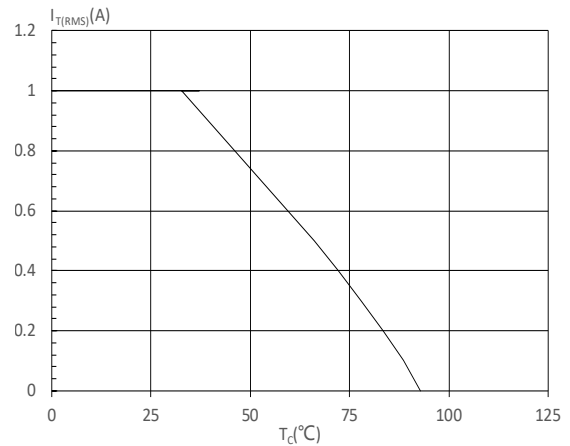
DELIVERY MODE

PACKAGE	OUTLINE	TUBE (PCS)
BT131	/	/

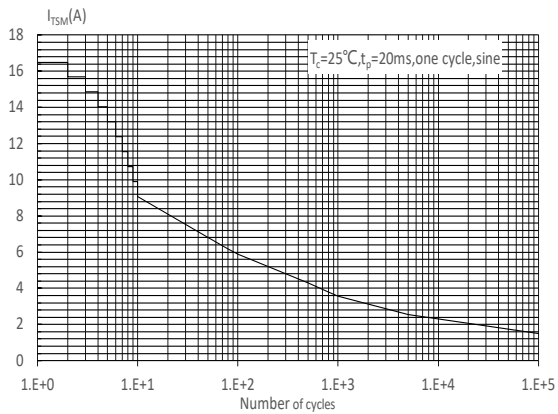
**FIG.1** Maximum power dissipation versus RMS on-state current



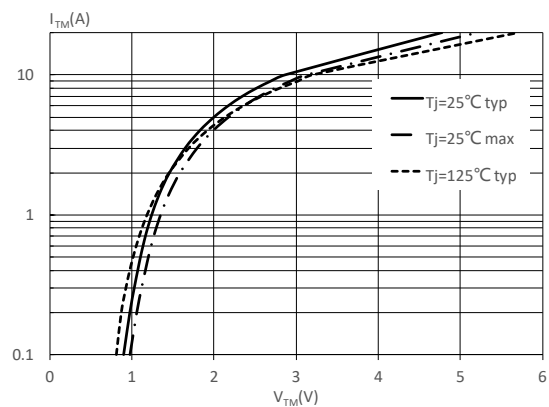
**FIG.2:** RMS on-state current versus case temperature



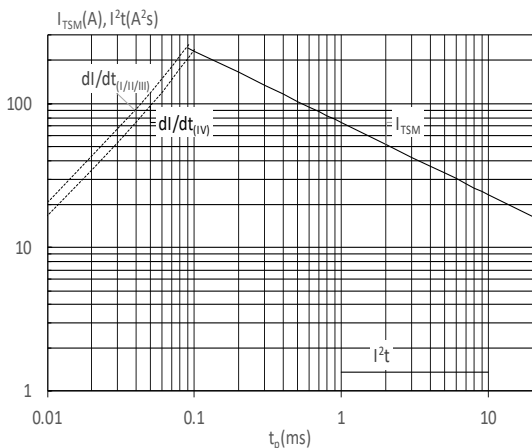
**FIG.3:** Surge peak on-state current versus number of cycles



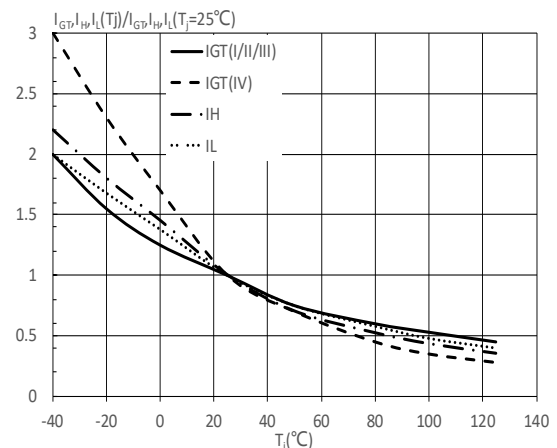
**FIG.4:** On-state characteristics



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p$  and value of  $I^2t$  (I - II - III:  $di/dt < 50A/\mu s$ ; IV:  $di/dt < 30A/\mu s$ )



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature



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[>>ZG\(中鑫半导体\)](#)